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March 2016

# FGH40T70SHD 700 V, 40 A Field Stop Trench IGBT

### **Features**

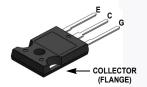
- Maximum Junction Temperature: T<sub>J</sub> =175°C
- · Positive Temperaure Co-efficient for Easy Parallel Operating
- · High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 1.7 \text{ V(Typ.)} @ I_C = 40 \text{ A}$
- 100% of the Parts Tested for I<sub>LM</sub>(1)
- · High Input Impedance
- · Fast Switching
- · Tighten Parameter Distribution
- · RoHS Compliant

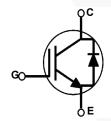
### **General Description**

Using novel field stop IGBT technology, Fairchild's new series of field stop 3<sup>rd</sup> generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.

### **Applications**

· Solar Inverter, UPS, Welder, Telecom, ESS, PFC





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description		FGH40T70SHD_F155	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		700	V
V	Gate to Emitter Voltage		± 20	V
$V_{GES}$	Transient Gate to EmitterVoltage		± 30	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	80	А
	Collector Current	@ T <sub>C</sub> = 100°C	40	Α
I <sub>LM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	120	Α
I <sub>CM (2)</sub>	Pulsed Collector Current		120	Α
I <sub>F</sub>	Diode Forward Current	@ T <sub>C</sub> = 25°C	40	Α
	Diode Forward Current	@ T <sub>C</sub> = 100°C	20	Α
I <sub>FM (2)</sub>	Pulsed Diode Maximum Forward Currer	it	120	Α
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	268	W
. 0	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	134	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +175	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

#### Notes:

- 1.  $V_{CC}$  = 400 V,  $V_{GE}$  = 15 V,  $I_{C}$  =120 A,  $R_{G}$  = 30  $\Omega$ , Inductive Load
- 2. Repetitive rating: Pulse width limited by max. junction temperature

### **Thermal Characteristics**

Symbol	Parameter	FGH40T70SHD_F155	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case, Max.	0.56	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case, Max.	1.71	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/W

# Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH40T70SHD_F155	FGH40T70SHD	TO-247 G03	Tube	N/A	N/A	30

### Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE}$ = 0V, $I_C$ = 1 mA	700	-	-	V
ΔBV <sub>CES</sub> / ΔΤ <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	I <sub>C</sub> = 1 mA, Reference to 25°C	-	0.6	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μА
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0 V	- \	_	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 40 mA, V <sub>CE</sub> = V <sub>GE</sub>	4.0	5.5	7.5	V
()		I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V	-	1.7	2.15	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 175°C	-	2.37	-	V
Dynamic C	Characteristics					
C <sub>ies</sub>	Input Capacitance		-	2028	-	pF
C <sub>oes</sub>	Output Capacitance	V <sub>CE</sub> = 30 V <sub>,</sub> V <sub>GE</sub> = 0 V, f = 1MHz	-	75	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 - 11VII 12	-	26	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-/	22	-	ns
t <sub>r</sub>	Rise Time		-	40	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> = 400 V, I <sub>C</sub> = 40 A,	-	66	->/	ns
t <sub>f</sub>	Fall Time	$R_G = 6 \Omega$ , $V_{GE} = 15 V$ ,	-	10	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	1150	// <b>-</b>	uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	271	- //	uJ
E <sub>ts</sub>	Total Switching Loss		-	1421	-	uJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	20	- \	ns
t <sub>r</sub>	Rise Time		-	36	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 40 \text{ A},$	-	68	-	ns
t <sub>f</sub>	Fall Time	$R_G = 6 \Omega$ , $V_{GE} = 15 V$ , Inductive Load, $T_C = 175^{\circ}C$	-	13	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, IC = 1/5 C	-	1760	1	uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	455	-	uJ
E <sub>ts</sub>	Total Switching Loss		-	2215	-	uJ

# Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Qg	Total Gate Charge		-	69	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	V <sub>CE</sub> = 400 V, I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V	-	13	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	V GE - 10 V	-	26	-	nC

## Electrical Characteristics of the Diode $T_C = 25$ °C unless otherwise noted

Symbol	Parameter		Test Condition	n	s	Min.	Тур.	Max	Unit
Ven	V <sub>FM</sub> Diode Forward Voltage	I- =	20 A		T <sub>C</sub> = 25°C	-	2.0	2.5	V
FIM		1F - 20 A			T <sub>C</sub> = 175°C	-	1.73	-	•
E <sub>rec</sub>	Reverse Recovery Energy				T <sub>C</sub> = 175°C	-	54	-	uJ
t	Diode Reverse Recovery Time	$I_F = 20 \text{ A}, dI_F/dt = 200 \text{ A}/\mu\text{s}$		T <sub>C</sub> = 25°C	-	37	-	ns	
۲rr				T <sub>C</sub> = 175°C	-	235	-	110	
Q <sub>rr</sub>	Diode Reverse Recovery Charge				T <sub>C</sub> = 25°C	-	65	-	nC
~11	2.000 No. 0.00 No. 000 Vol.y Onlargo				T <sub>C</sub> = 175°C	-	944	-	

**Figure 1. Typical Output Characteristics** 

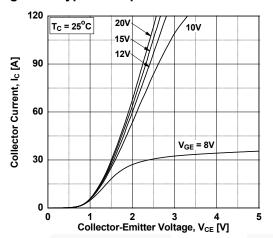


Figure 3. Typical Saturation Voltage Characteristics

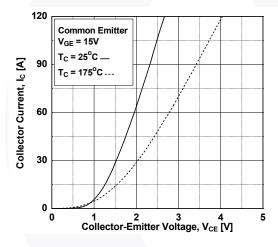
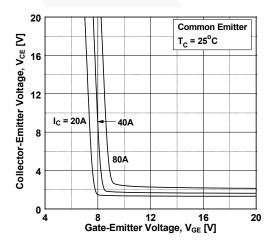


Figure 5. Saturation Voltage vs. V<sub>GE</sub>



**Figure 2. Typical Output Characteristics** 

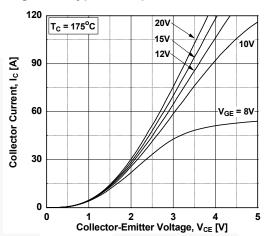


Figure 4. Saturation Voltage vs. Case
Temperature at Variant Current Level

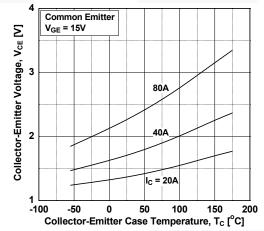


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

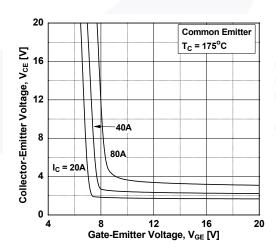


Figure 7. Capacitance Characteristics

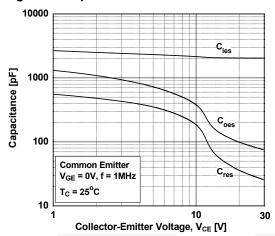


Figure 9. Turn-on Characteristics vs.
Gate Resistance

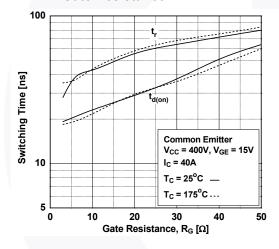


Figure 11. Switching Loss vs.
Gate Resistance

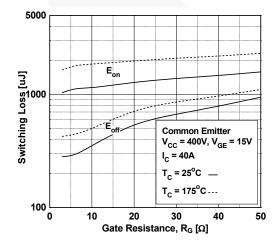


Figure 8. Gate charge Characteristics

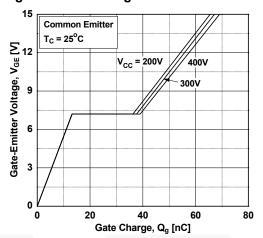


Figure 10. Turn-off Characteristics vs. Gate Resistance

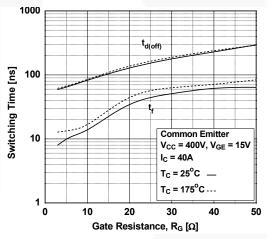


Figure 12. Turn-on Characteristics vs. Collector Current

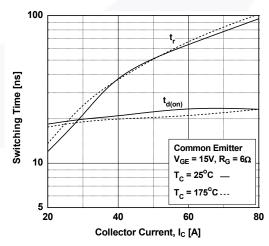


Figure 13. Turn-off Characteristics vs. Collector Current

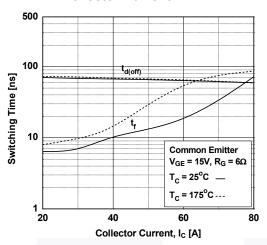


Figure 15. Load Current Vs. Frequency

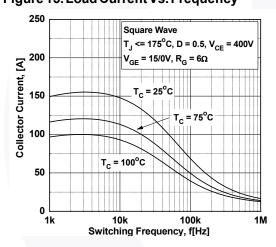


Figure 17. Forward Characteristics

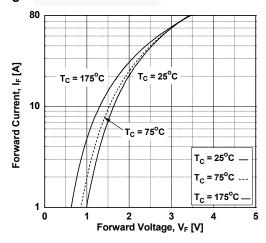


Figure 14. Switching Loss vs. Collector Current

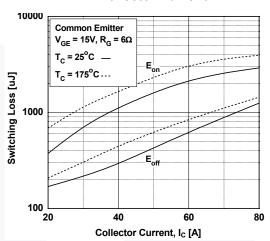


Figure 16. SOA Characteristics

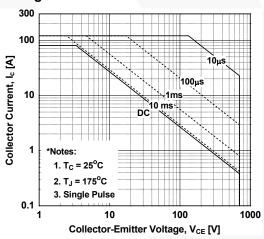


Figure 18. Reverse Recovery Current

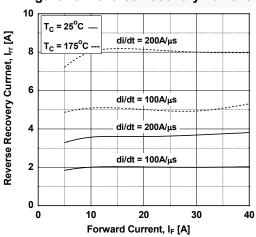


Figure 19. Reverse Recovery Time

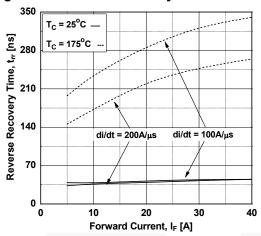


Figure 20. Stored Charge

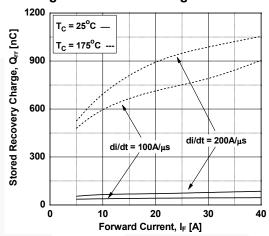


Figure 21.Transient Thermal Impedance of IGBT

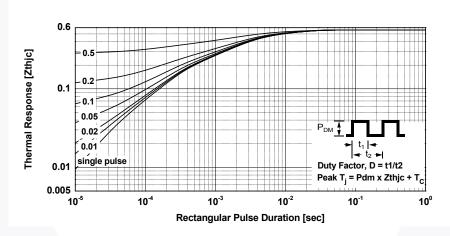
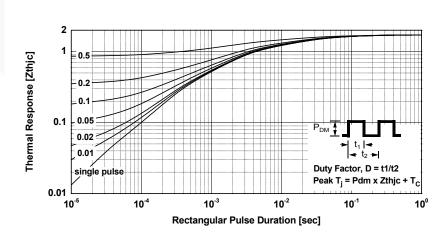


Figure 22. Transient Thermal Impedance of Diode



#### **Mechanical Dimensions**

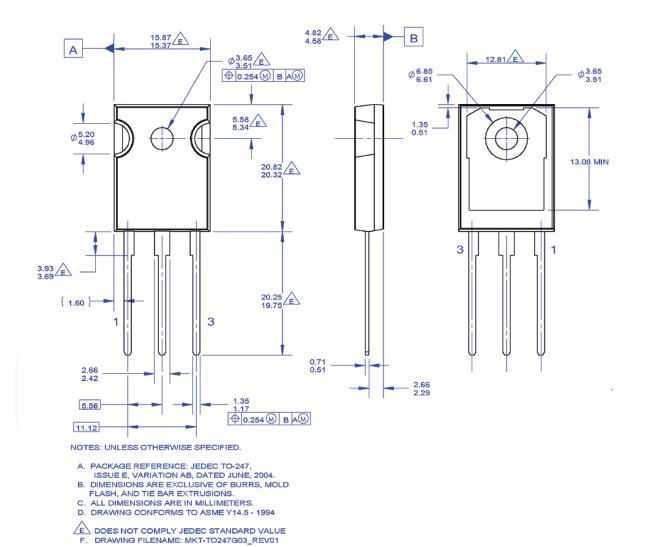


Figure 23. TO-247 3L - TO-247, MOLDED, 3 LEADS, JEDEC AB LONG LEADS

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